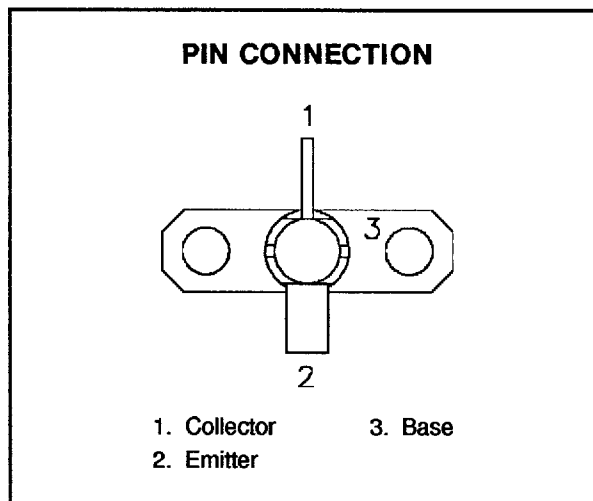
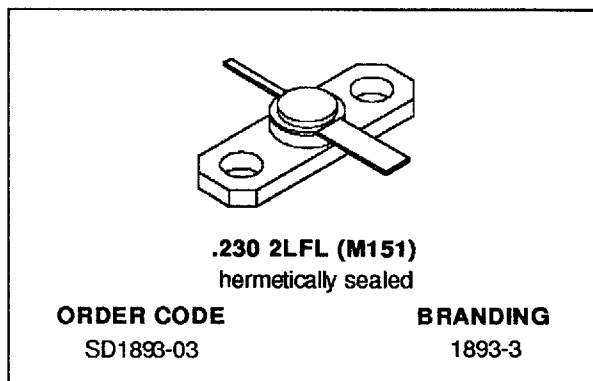


RF & MICROWAVE TRANSISTORS
1.6 GHZ SATCOM APPLICATIONS

- 1.65 GHz
- 28 VOLTS
- OVERLAY DIE GEOMETRY
- GOLD METALLIZATION
- HIGH RELIABILITY AND RUGGEDNESS
- P_{OUT} = 10 W MIN. WITH 11.0 dB GAIN
- COMMON BASE



DESCRIPTION

The SD1893-03 is a 28 V silicon NPN planar transistor designed for INMARSAT and other 1.6 GHz SATCOM applications. The device utilizes polysilicon site ballasting with a gold metallized die to achieve high reliability and ruggedness.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	45	V
V _{CEO}	Collector-Emitter Voltage	15	V
V _{EBO}	Emitter-Base Voltage	3.5	V
I _C	Device Current	4.4	A
P _{DISS}	Power Dissipation	43	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	5.5	°C/W
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ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)

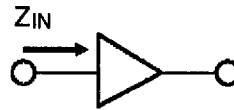
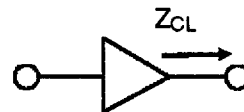
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_{\text{C}} = 3\text{mA}$	$I_{\text{E}} = 0\text{mA}$	45	—	—	V
BV_{EBO}	$I_{\text{E}} = 3\text{mA}$	$I_{\text{C}} = 0\text{mA}$	3.5	—	—	V
I_{CBO}	$V_{\text{CB}} = 28\text{V}$	$I_{\text{E}} = 0\text{mA}$	—	—	5	mA
h_{FE}	$V_{\text{CE}} = 5\text{V}$	$I_{\text{C}} = 300\text{mA}$	15	—	150	—

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 1.65\text{ GHz}$	$P_{\text{IN}} = 0.6\text{ W}$	$V_{\text{CE}} = 28\text{ V}$	10	—	—	W
G_{P}	$f = 1.65\text{ GHz}$	$P_{\text{IN}} = 0.6\text{ W}$	$V_{\text{CE}} = 28\text{ V}$	11	—	—	dB
η_{c}	$f = 1.65\text{ GHz}$	$P_{\text{IN}} = 0.6\text{ W}$	$V_{\text{CE}} = 28\text{ V}$	45	—	—	%
C_{OB}	$f = 1\text{ MHz}$	$V_{\text{CB}} = 28\text{ V}$		—	19	—	pF

IMPEDANCE DATA

TYPICAL INPUT
IMPEDANCETYPICAL COLLECTOR
LOAD IMPEDANCE

FREQ.	Z_{IN} (Ω)	Z_{CL} (Ω)
1.5 GHz	$2.5 + j 4.5$	$3.5 - j 2.6$
1.6 GHz	$2.0 + j 6.0$	$3.0 - j 3.3$
1.7 GHz	$2.0 + j 7.0$	$3.5 - j 4.0$

TEST CIRCUIT

C1, C2 : .4 - 2.5pF Johanson Capacitor #27283
C3 : 100pF Chip Capacitor ATC 100 A101KCA 150
C4 : 15,000pF EMI Filter Murata/Erie 9900-381-6004

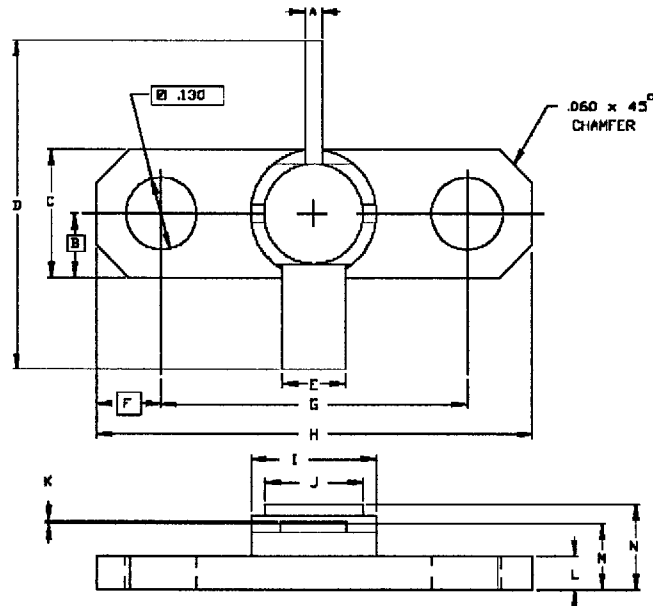
L1, L2 : 4 Turn, Choke #28 AWG .080" I.D.

Board

Material: Epsilam 10, Er = 10.2, H = .050"
1 Oz. Cu, SMA Launcher CDI (2 poeces)
.230" Fixture Housing Heatsink, Advanced Corp. 5308-2CC

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0151



SGS-THOMSON MICROELECTRONICS			CONT'D	
	MINIMUM Inches/mm	MAXIMUM Inches/mm	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.025/0,64	.035/0,89	K	.003/0,08
B	.115/2,92	NOM.	L	.055/1,40
C	.225/5,72	.235/5,97	M	.120/3,18
D	.710/18,03	.750/19,05	N	.140/3,56
E	.110/2,79	.120/3,05		
F	.120/3,05	NOM.		
G	.555/14,10	.565/14,35		
H	.795/20,19	.805/20,45		
I	.222/5,64	.236/5,99		
J	.165/4,19	.185/4,70		

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